



# STATIC RAM

☆ New product  
★ Under development

## ■ STATIC RAMs

### ◆ Features

- The product lineup includes a wide variety of bit configurations (×4, ×8, ×16, ×18, ×32).
- High-speed synchronous devices for the secondary cache memory are available for use with low-voltage, low-power CPUs ideal for portable equipment.

Features	Capacity	Bit configuration	Model No.	Access time (ns) MAX Cycle time (ns) MAX.	Supply current MAX.		Supply voltage (V)	Operating temperature (°C)	Package
					Operating (mA)	Standby (mA)			
Low voltage operation	16k	× 8	LH5116SN	1 000	10	0.001	2.7 to 3.3	0 to 50	24SOP
	64k	× 8	LH5164AVN/AVT	200	45	0.001	2.7 to 5.5	-10 to 70	28SOP/28TSOP(I)*11
			LH5164AV3HN	200	50	0.001*4	2.7 to 5.5	-40 to 85	28SOP
			LH5164AVHN/AVHT	200	25	0.001*4	3.0 to 3.6	-40 to 85	28SOP/28TSOP(I)*11
			LH5164AST	500	20	0.001	2.5 to 5.5	-10 to 70	28TSOP(I)*11
			LH5164ASHN/ASHT	500	20	0.001*4	2.5 to 5.5	-40 to 85	28SOP/28TSOP(I)*11
	256k	× 8	LH51V256N/T-85SL	250*1/85*2	25	0.003	1.8 to 3.6	0 to 70	28SOP/28TSOP(I)*11
			LH51V256HN/HT-85SL	250*1/85*2	25	0.005	1.8 to 3.6	-40 to 85	28SOP/28TSOP(I)*11
			☆ LH52CV256N/T-10LL	100	15	0.025	2.7 to 3.6	0 to 70	28SOP/28TSOP(I)*11
			☆ LH52CV256JN/JT-10LL	100	15	0.025	2.7 to 3.6	-25 to 85	28SOP/28TSOP(I)*11
			☆ LH52CV256HN/HT-10LL	100	15	0.025	2.7 to 3.6	-40 to 85	28SOP/28TSOP(I)*11
			LH52256CVN/CVT	200*2/150*3	15	0.02	2.7 to 3.6	0 to 70	28SOP/28TSOP(I)*11
			★ LH52256CVJN/CVJT	200	15	0.04	2.7 to 3.6	-25 to 85	28SOP/28TSOP(I)*11
	1M	× 8	LH52256CSN/CST	500	10	0.02	2.5 to 3.6	0 to 70	28SOP/28TSOP(I)*11
			☆ LH5BV1000JY-70L	70	30	0.06	2.7 to 3.6	-25 to 85	32FBGA(CSP)*10
		× 16	LH52D1000T/S-85LL/10LL	85/100	40	0.045	2.7 to 3.6	-25 to 85	32TSOP(I)*11/32TSOP(I)*8, *11
			★ LH51V1016JS/JY-70LL/85LL	70/85	45	0.025	2.7 to 3.6	-25 to 85	40TSOP(I)*11/48FBGA(CSP)*9
	2M	× 8	★ LH59BV2000JS-70L	70	35	0.1	2.7 to 3.6	-25 to 85	32TSOP(I)*8, *11
			★ LH51V2008JS/JY-70LL/85LL	70/85	45	0.05	2.7 to 3.6	-25 to 85	32TSOP(I)*8, *11/32FBGA(CSP)*10
	5-V operation	16k	× 8	LH5116/NA/D-10	100	40	0.001	4.5 to 5.5	0 to 70
LH5116H/HN/HD-10				100	40	0.001	4.5 to 5.5	-40 to 85	24DIP/24SOP/ 24SK-DIP
64k		× 8	LH5164A/AN-80L	80	55	0.001	4.5 to 5.5	-10 to 70	28DIP/28SOP
			LH5164A/AN/AD/AT-10L	100	45	0.001	4.5 to 5.5	-10 to 70	28DIP/28SOP/28SK-DIP/28TSOP(I)*11
			LH5164AH/AHN/AHD/AHT-10L	100	50	0.001*4	4.5 to 5.5	-40 to 85	28DIP/28SOP/28SK-DIP/28TSOP(I)*11
			LH5268A/AN/AD-10LL	100	40	0.04	4.5 to 5.5	0 to 70	28DIP/28SOP/28SK-DIP
256k		× 8	LH52256C/CN/CD/CT-70LL/85LL/10LL	70/85/100	45/40/40	0.04	4.5 to 5.5	0 to 70	28DIP/28SOP/28SK-DIP/28TSOP(I)*11
			LH52256CH/CHN/CHT-70LL/85LL/10LL	70/85/100	45/40/40	0.04	4.5 to 5.5	-45 to 85	28DIP/28SOP/28TSOP(I)*11
512k		× 8	LH52512N-85LL/10LL	85/100	50	0.05	4.5 to 5.5	0 to 70	32SOP
High speed		1M	× 4	LH521002AK-20/25	20/25	140/130	2	4.5 to 5.5	0 to 70
	× 8		LH521007AK-20/25	20/25	180/175	2	4.5 to 5.5	0 to 70	32SOJ (400 mil.)
	× 18		LH521028AU-15/17/20/25	15/17/20/25	300	4	4.5 to 5.5	0 to 70	52QFJ
Synchronous SRAM	1M	× 32	LH51V1032C4M-15/17	8/9*5, 15/17*6	220/200	2	3.3 ±5%	0 to 70	100LQFP

\*1 1.8 V ≤ Vcc ≤ 3.6 V  
\*2 2.7 V ≤ Vcc ≤ 3.6 V  
\*3 3.0 V ≤ Vcc ≤ 3.6 V

\*4 At Ta = 0 to 70°C  
\*5 Access time  
\*6 Cycle time

\*7 Nominal dimensions: 8 x 13.4 mm, pin pitch: 0.4 mm  
\*8 Nominal dimensions: 8 x 13.4 mm, pin pitch: 0.5 mm  
\*9 Nominal dimensions: 6 x 8 mm

\*10 Nominal dimensions: 6 x 10 mm  
\*11 Normal bend

Memories